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Microsemi

Power Matters[™]

1.00

100.00

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Overview **Diagrams**

Collector to Emitter Saturation Voltage

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			80.00	V
Collector Current (dc)	I _C			10.00	А
Collector-Emitter Voltage (Base Open)	V_{CEO}			80.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			6.00	V
Power Dissination Total	P _T			150 00	W

V_{CE(sat)}

HFE

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- $\bullet \ \ \, \text{Non-Radiation Hardened Devices} \ \bullet \ \, \text{Transistors} \ \bullet \ \, \text{BJT(BiPolar Junction Transistor)} \ \bullet \ \, \text{PNP Transistor}$

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